

# **Excellent Integrated System Limited**

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Vishay/Siliconix SIR644DP-T1-GE3

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**Distributor of Vishay/Siliconix: Excellent Integrated System Limited** Datasheet of SIR644DP-T1-GE3 - MOSFET N-CH 40V 60A PPAK SO-8 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



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### SPICE Device Model SiR644DP

Vishay Siliconix

## N-Channel 40 V (D-S) MOSFET

### DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### **CHARACTERISTICS**

- N-Channel Vertical DMOS
- Macro Model (Sub-circuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

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### SUBCIRCUIT MODEL SCHEMATIC

#### Note

 This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},\ I_{D}=250\ \mu A$	1.7	-	V
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	0.0022	0.0022	Ω
		$V_{GS}=4.5 \text{ V}, \text{ I}_{D}=15 \text{ A}$	0.0030	0.0030	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	88	87	S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 5 A	0.74	0.74	V
Dynamic <sup>b</sup>					
Input Capacitance	C <sub>iss</sub>	$V_{DS}$ = 20 V, $V_{GS}$ = 0 V, f = 1 MHz	3090	3200	pF
Output Capacitance	Coss		2180	2200	
Reverse Transfer Capacitance	C <sub>rss</sub>		159	160	
Total Gate Charge	Qg	$V_{DS}$ = 20 V, $V_{GS}$ = 10 V, $I_{D}$ = 20 A	46	47	- nC
		$V_{DS}$ = 20 V, $V_{GS}$ = 4.5 V, $I_{D}$ = 20 A	22	21.3	
Gate-Source Charge	Q <sub>gs</sub>		7.5	7.5	
Gate-Drain Charge	Q <sub>gd</sub>		12	12	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

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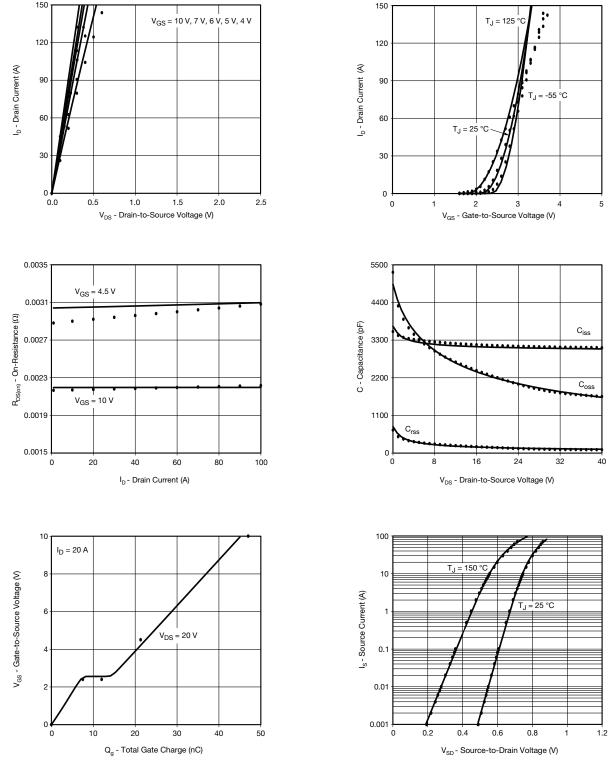


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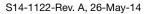
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#### Note

• Dots and squares represent measured data. Copyright: Vishay Intertechnology, Inc.



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